

Cite this: *Nanoscale*, 2022, **14**, 5247

Correction: Strain mapping inside an individual processed vertical nanowire transistor using scanning X-ray nanodiffraction

Dmitry Dzhigaev,^{*a} Johannes Svensson,^b Abinaya Krishnaraja,^b Zhongyunshen Zhu,^b Zhe Ren,^a Yi Liu,^a Sebastian Kalbfleisch,^c Alexander Björling,^c Filip Lenrick,^a Zoltan Imre Balogh,^d Susanna Hammarberg,^a Jesper Wallentin,^a Rainer Timm,^a Lars-Erik Wernersson^b and Anders Mikkelsen^a

Correction for 'Strain mapping inside an individual processed vertical nanowire transistor using scanning X-ray nanodiffraction' by Dmitry Dzhigaev *et al.*, *Nanoscale*, 2020, **12**, 14487–14493, DOI: [10.1039/DONR02260H](https://doi.org/10.1039/DONR02260H).

DOI: [10.1039/d2nr90060b](https://doi.org/10.1039/d2nr90060b)

rsc.li/nanoscale

The authors regret that the Acknowledgements section in the original manuscript was incorrect. The Acknowledgements should read as follows:

Acknowledgements

We acknowledge MAX IV Laboratory for time on Beamline NanoMAX under Proposal 20180047. Research conducted at MAX IV, a Swedish national user facility, is supported by the Swedish Research council under contract 2018-07152, the Swedish Governmental Agency for Innovation Systems under contract 2018-04969, and Svenska Forskningsrådet Formas under contract 2019-02496.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.



^aDivision of Synchrotron Radiation Research and NanoLund, Department of Physics, Lund University, P.O. Box 118, SE-221 00 Lund, Sweden.
E-mail: dmitry.dzhigaev@slfus.lu.se

^bElectrical and Information Technology, Department of Engineering, Lund University, P.O. Box 118, SE-221 00 Lund, Sweden

^cMAX IV Laboratory, Lund University, 22100 Lund, Sweden

^dDTU CEN, DTU, Fysikvej 2800, Lyngby, Denmark